# International

#### HEXFRED<sup>™</sup>

#### Features

- Ultrafast Recovery
- Ultrasoft Recovery
- Very Low I<sub>RRM</sub>
- Very Low Qrr
- Guaranteed Avalanche
- · Specified at Operating Conditions

#### **Benefits**

- Reduced RFI and EMI
- Reduced Power Loss in Diode and Switching Transistor
- Higher Frequency Operation
- Reduced Snubbing
- Reduced Parts Count

#### Description

International Rectifier's HFA04TB60S is a state of the art ultra fast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 volts and 8 amps per Leg continuous current, the HFA04TB60S is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultra fast recovery time, the HEXFRED product line features extremely low values of peak recovery current (I<sub>RRM</sub>) and does not exhibit any tendency to "snap-off" during the  $t_{\text{b}}$  portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED HFA04TB60S is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

#### Absolute Maximum Ratings

	Parameter	Max.	Units
V <sub>R</sub>	Cathode-to-Anode Voltage	600	V
I <sub>F</sub> @ T <sub>C</sub> = 100°C	Continuous Forward Current	4.0	
I <sub>FSM</sub>	Single Pulse Forward Current	25	А
I <sub>FRM</sub>	Maximum Repetitive Forward Current	16	7
$P_D @ T_C = 25^{\circ}C$	Maximum Power Dissipation	25	w
P <sub>D</sub> @ T <sub>C</sub> = 100°C	Maximum Power Dissipation	10	_ vv
TJ	Operating Junction and	55 to 1150	°C
T <sub>STG</sub>	Storage Temperature Range	-55 to +150	

## HFA04TB60S

Ultrafast, Soft Recovery Diode

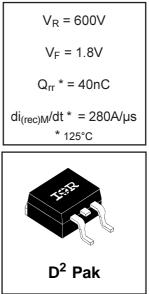
(K)

BASE

(N/C) ↓<sup>1</sup>

2

<sup>3</sup> (A)



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	Parameter	Min.	Тур.	Max.	Units	Test Conditions	
$V_{BR}$	Cathode Anode Breakdown Voltage	600			V	I <sub>R</sub> = 100μA	
V <sub>FM</sub>	Max Forward Voltage		1.5	1.8	V	I <sub>F</sub> = 4.0A	
			1.8	2.2		I <sub>F</sub> = 8.0A See Fig. 1	
			1.4	1.7		I <sub>F</sub> = 4.0A, T <sub>J</sub> = 125°C	
I <sub>RM</sub>	Max Reverse Leakage Current		0.17	3.0	μA	$V_R = V_R$ Rated See Fig. 2	
			44	300	μΛ	$T_J = 125^{\circ}C, V_R = 0.8 \times V_R Rated$	
CT	Junction Capacitance		4.0	8.0	pF	V <sub>R</sub> = 200V See Fig. 3	
L <sub>S</sub>	Series Inductance		8.0		nH	Measured lead to lead 5mm from	
	Series inductance					package body	

#### Electrical Characteristics @ $T_J = 25^{\circ}C$ (unless otherwise specified)

#### Dynamic Recovery Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Тур.	Max.	Units	Test Conditions		
trr	Reverse Recovery Time		17			$I_F$ = 1.0A, di <sub>f</sub> /dt = 200A/µs, $V_R$ = 30V		
t <sub>rr1</sub>	See Fig. 5 & 6		28	42	ns	T <sub>J</sub> = 25°C		
t <sub>rr2</sub>	-		38	57		T <sub>J</sub> = 125°C	I <sub>F</sub> = 4.0A	
I <sub>RRM1</sub>	Peak Recovery Current		2.9	5.2	Α	T <sub>J</sub> = 25°C		
I <sub>RRM2</sub>			3.7	6.7		T <sub>J</sub> = 125°C	V <sub>R</sub> = 200V	
Q <sub>rr1</sub>	Reverse Recovery Charge		40	60	nC	T <sub>J</sub> = 25°C		
Q <sub>rr2</sub>	See Fig. 7		70	105		T <sub>J</sub> = 125°C	di <sub>f</sub> /dt = 200A/µs	
di <sub>(rec)M</sub> /dt1	Peak Rate of Fall of Recovery Current		280		A/µs	$T_J = 25^{\circ}C$		
di <sub>(rec)M</sub> /dt2	During t <sub>b</sub> See Fig. 8		235		μs	T <sub>J</sub> = 125°C		

#### **Thermal - Mechanical Characteristics**

	Parameter	Min.	Тур.	Max.	Units
T <sub>lead</sub> ①	Lead Temperature			300	°C
R <sub>thJC</sub>	Thermal Resistance, Junction to Case			5.0	K/W
R <sub>thJA</sub> ②	Thermal Resistance, Junction to Ambient			80	17/17
Wt	Weight		2.0		g
			0.07		(oz)

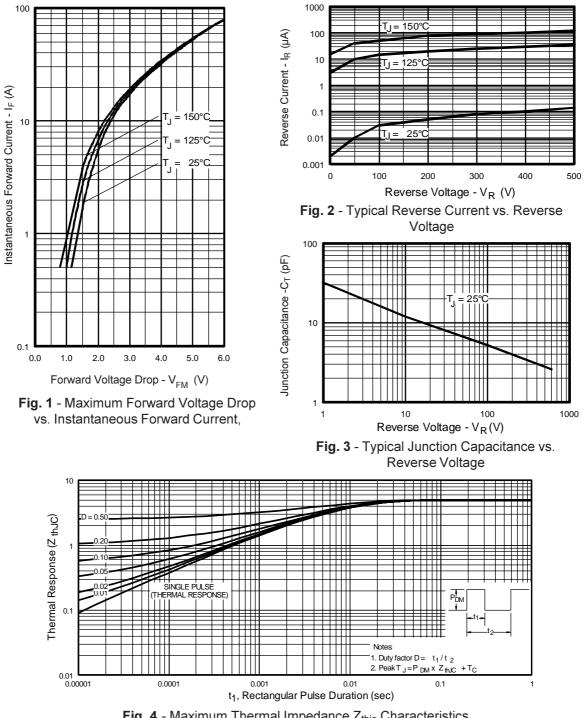
① 0.063 in. from Case (1.6mm) for 10 sec

② Typical Socket Mount

#### International **TOR** Rectifier

## HFA04TB60S

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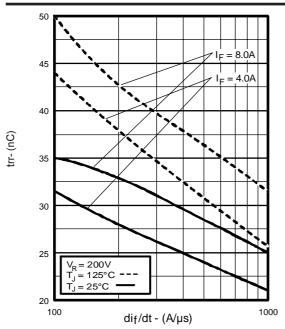


Fig. 5 - Typical Reverse Recovery vs. dif/dt

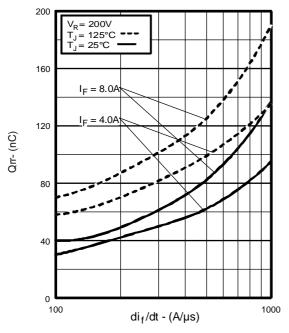


Fig. 7 - Typical Stored Charge vs. dif/dt

International **10R** Rectifier

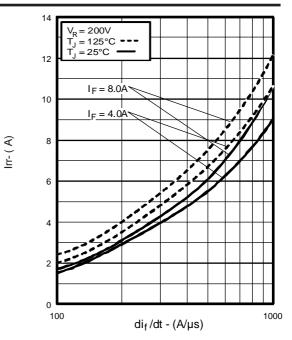
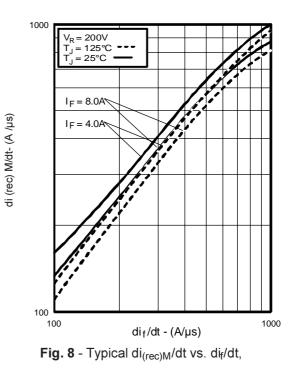
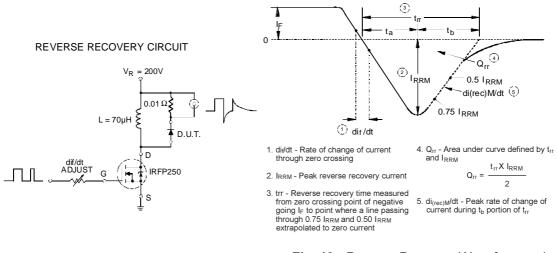
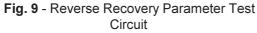


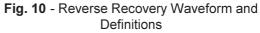
Fig. 6 - Typical Recovery Current vs. dif/dt



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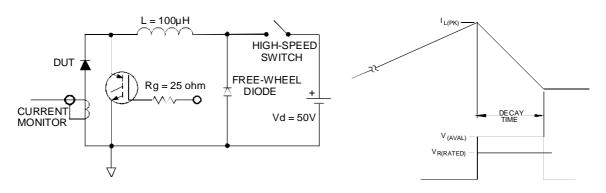
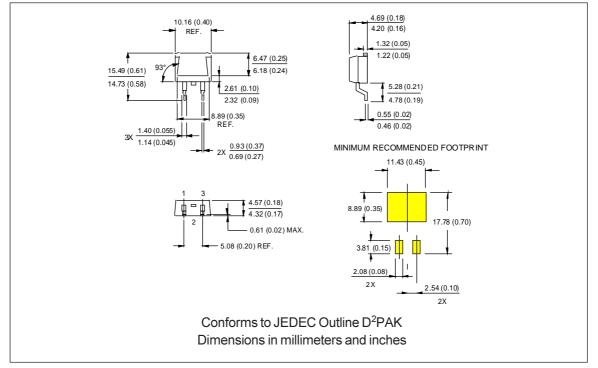


Fig. 11 - Avalanche Test Circuit and Waveforms

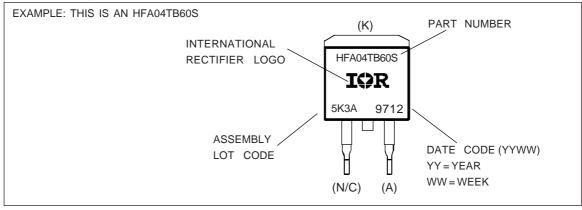
International **IOR** Rectifier

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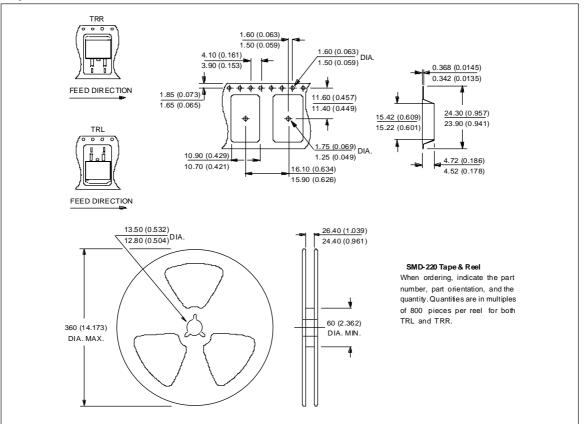
#### **Outline Table**



#### **Part Marking Information**



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#### **Tape & Reel Information**

## International

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Data and specifications subject to change without notice.

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